## AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

- 1. (Currently Amended) A polishing system comprising:
  - (a) a liquid carrier,
- (b) a <u>branched</u> polymer having a degree of branching of about 50% or greater, and
  - (c) a polishing pad, an abrasive, or a combination thereof.
- 2. (Original) The polishing system of claim 1, wherein the degree of branching is about 60% or greater.
- 3. (Original) The polishing system of claim 2, wherein the degree of branching is about 70% or greater.
- 4. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer is selected from the group consisting of dendritic polymers, comb polymers, bottle-brush polymers, linear-dendrimer diblock copolymers, linear-dendrimer triblock copolymers, random-branched polymers, copolymers thereof, and combinations thereof.
- 5. (Currently Amended) The polishing system of claim 4, wherein the <u>branched</u> polymer is a linear-dendrimer diblock copolymer.
- 6. (Original) The polishing system of claim 5, wherein the linear-dendrimer diblock copolymer is a polyethylene oxide-polyamidoamine (PEO-PAMAM) diblock copolymer.
- 7. (Currently Amended) The polishing system of claim 4, wherein the <u>branched</u> polymer is a linear-dendrimer triblock copolymer.

- 8. (Original) The polishing system of claim 7, wherein the linear-dendrimer triblock copolymer is a polyethylene oxide-polypropylene oxide-polyamidoamine triblock copolymer.
- 9. (Currently Amended) The polishing system of claim 4, wherein the <u>branched</u> polymer is a dendritic polymer.
- 10. (Original) The polishing system of claim 9, wherein the dendritic polymer comprises a core monomer selected from the group consisting of a  $C_{1-8}$  heterocyclic ring, a  $C_{1-8}$  carbocyclic ring, a  $C_{1-8}$  alkane, and a  $C_{1-8}$  aminoalkane.
- 11. (Original) The polishing system of claim 9, wherein the dendritic polymer branches from a nitrogen atom.
- 12. (Original) The polishing system of claim 9, wherein the dendritic polymer comprises about 2 to about 10 generations.
- 13. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer is a polyamidoamine (PAMAM) polymer.
- 14. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer is a polyglycerol.
- 15. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer comprises surface functional groups selected from the group consisting of amines, amides, carboxylic acids, sulfonic acids, phosphonic acids, hydroxyl groups, salts thereof, and combinations thereof.
- 16. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer has a molecular weight of about 1,000 to about 1,000,000 g/mol.

- 17. (Original) The polishing system of claim 16, wherein the molecular weight is about 2,000 to about 500,000 g/mol.
- 18. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer comprises a highly branched core comprising monomers, wherein about 50% or more of the monomers within the highly branched core are branched.
- 19. (Currently Amended) The polishing system of claim 1, wherein the <u>branched</u> polymer has a viscosity that is about 70% or less the viscosity of a linear polymer of the same monomer composition and molecular weight under the same conditions.
- 20. (Original) The polishing system of claim 1, wherein the system comprises an abrasive suspended in the liquid carrier.
- 21. (Original) The polishing system of claim 1, wherein the system comprises an abrasive fixed to a polishing pad.
- 22. (Original) The polishing system of claim 1, further comprising one or more polishing additives selected from the group consisting of chelating or complexing agents, oxidizing agents, surfactants, anti-foaming agents, biocides, and combinations thereof.
  - 23. (Withdrawn) A method of polishing a substrate comprising:
    - (i) contacting a substrate with the polishing system of claim 1, and
    - (ii) abrading at least a portion of the substrate to polish the substrate.